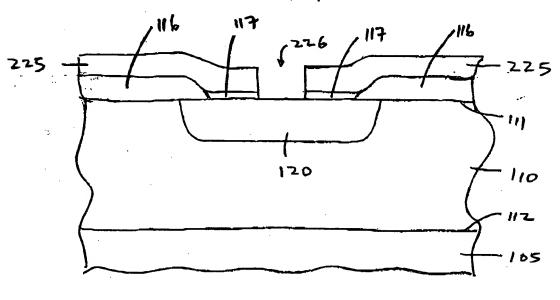
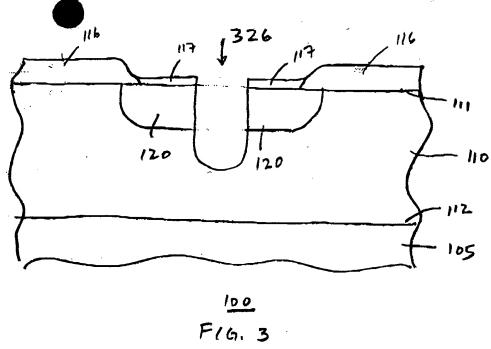
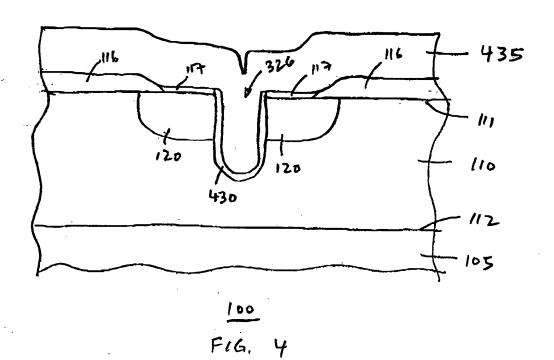


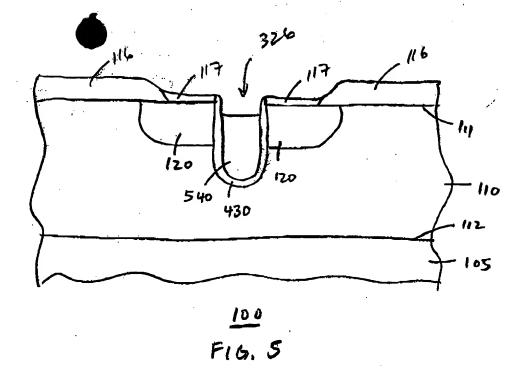
100 F16. 1

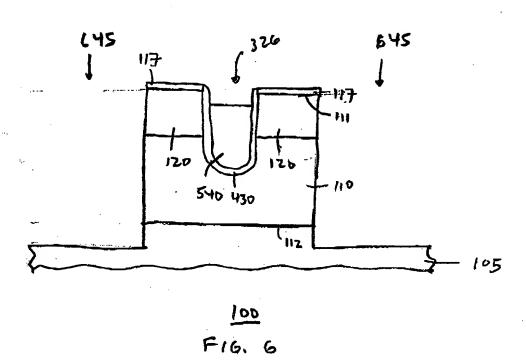


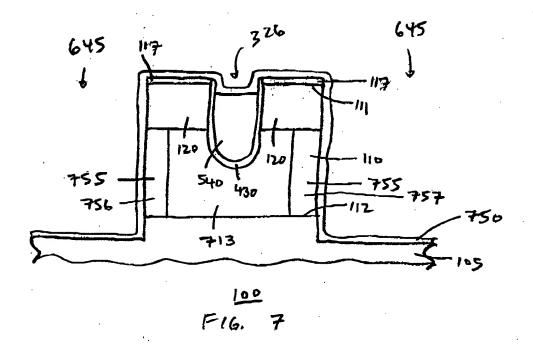
100 F16, 2

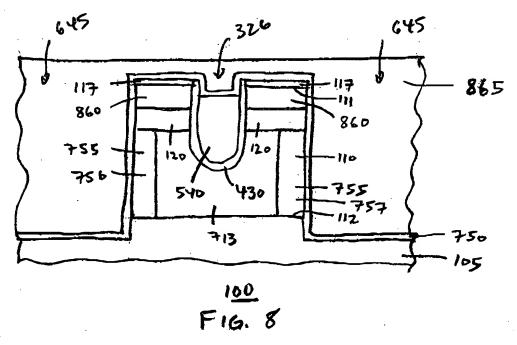


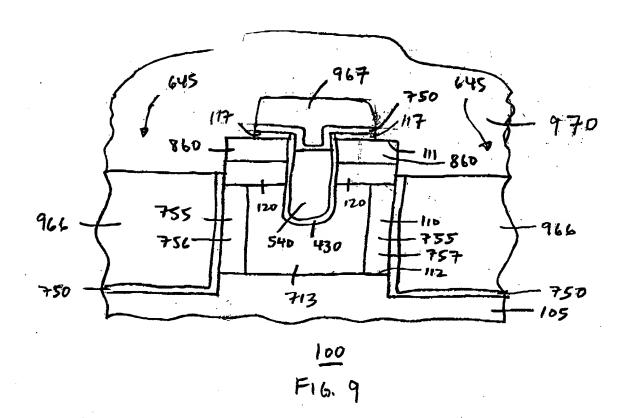


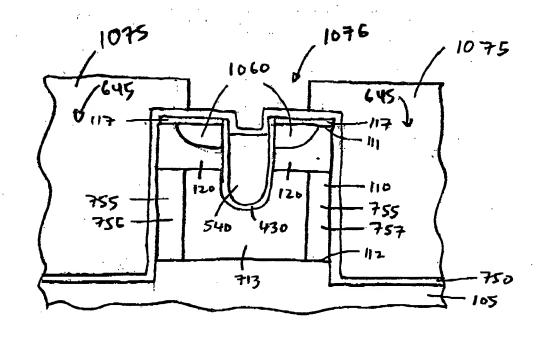




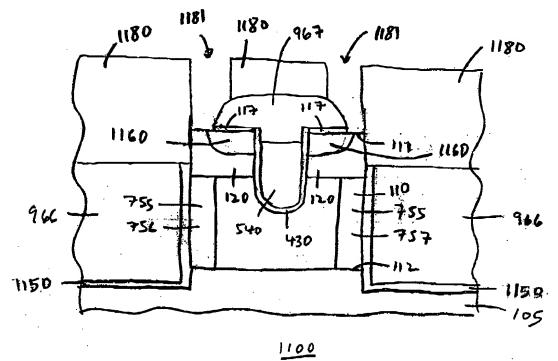




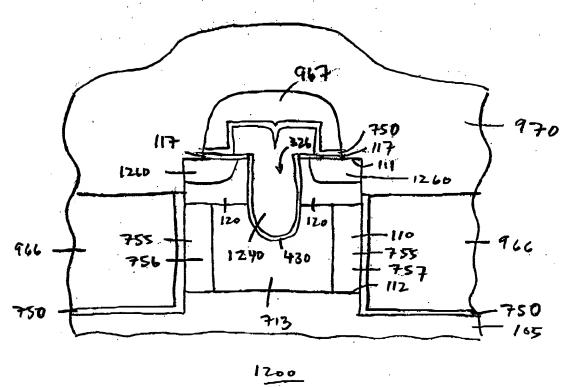




F16. 10



F16. 11



F16. 12

## FIG. 13

## 1300

1310	Providing a semiconductor layer over a semiconductor substrate
	<b>+</b>
1320	Forming a channel region in the semiconductor layer
	<b>1</b>
1330	Forming a first trench in the semiconductor layer
	1
1340	Forming a control electrode in the trench
	4
1350	Forming a second trench into the semiconductor layer
	. ↓
1360	Forming a charge balancing region in the semiconductor
_	<b>↓</b> :
1370	Forming a heavily doped region in the semiconductor layer
_	<b>↓</b>
1380	Forming an electrical contact coupled to the heavily doped region
_	<b>\</b> .
1390	Forming another electrical contact coupled to the semiconductor substrate

PX01DOCS/288545.01

**ATTORNEY-CLIENT PRIVILEGED**